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The invention relates to the silverless semiconductor photography and can be utilized in the holography, cinematography, micro and optoelectronics, computer engineering.

Summary of the invention: the information carrier contains a dielectric support 1 with the subsequently placed on it first electrode 2, a photoinjecting layer 3, a recording layer 4 of vitreous chalcogenic semiconductor and second electrode 5. The recording layer 4 is made of arsenic triselenide, doped with tin atoms of general formula $As_2Se_3Sn_x$, the tin atoms concentration with that is determined in the limits of $0,005 \leq x \leq 0,03$.

Claims: 1

Fig.: 2